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U.S. PATENT DOCUMENTS

Examiner Initial	Document No.	Name	Date	Class	Subclass	Filing Date (If appropriate)
_____	AA					
_____	AB					

FOREIGN PATENT DOCUMENTS

Examiner Initial	Document No.	Date	Country	Translation (Yes or No)
_____	AC			
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OTHER DOCUMENTS

SK	AE	E.P. Gusev et al., "Ultrathin high-K gate stacks for advanced CMOS devices," International Electron Devices Meeting Technical Digest (2001), pp. 451-454.
SK	AF	W. Zhu et al., "HfO ₂ and HfAlO for CMOS: Thermal Stability and Current Transport," International Electron Devices Meeting Technical Digest (2001), pp. 463-466.
SK	AG	Y. Tamura et al., "Electrical characteristics of SiO ₂ /High-k stacked gate insulator," Extended Abstracts (The 49 th Spring Meeting, 2002); The Japan Society of Applied Physics and Related Societies, No. 2, 28p-A-10, p.820.
Examiner 		Date Considered 8/18/05